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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/744,722	09/744,722 05/07/2001		Klaus Peter Crone	AG-6564	3395
23416	7590	01/14/2003			
		E LODGE & HU	EXAMINER		
1220 N MAR P O BOX 220		KEEI	MULPURI, SAVITRI		
WILMINGTON, DE 19899					
				ART UNIT	PAPER NUMBER
				2812	15
				DATE MAILED: 01/14/2003	

Please find below and/or attached an Office communication concerning this application or proceeding.

Application No.

Applicant(s)

09/744,722

piicarit(s)

Examiner

Office Action Summary

Savitri Mulpuri

Art Unit 2812

Crone et al



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The MAILING L Period for Reply	DATE of this communication appears	on the cover sheet with the corre	spondence address
A SHORTENED STATU	TORY PERIOD FOR REPLY IS SET F THIS COMMUNICATION.	TTO EXPIRE 3 MONT	H(S) FROM
 Extensions of time may be available 	able under the provisions of 37 CFR 1.136 (a), In	n no event, however, may a reply be timely file	d after SIX (6) MONTHS from the
If the period for reply specified a If NO period for reply is specified Failure to reply within the set or	on. bove is less than thirty (30) days, a reply within t dabove, the maximum statutory period will apply extended period for reply will, by statute, cause t later than three months after the mailing date of	the statutory minimum of thirty (30) days will be and will expire SIX (6) MONTHS from the mail	pe considered timely. ling date of this communication.
Status	333 37 3111 1.704(b).		
1) 💢 Responsive to co	mmunication(s) filed on <u>Dec 13, 2</u>	2002	
2a) This action is FIN	IAL. 2b) 💢 This ac	tion is non-final.	
3) Since this applica closed in accorda	ition is in condition for allowance on the state of the condition for allowance of the condition is a second to the condition of the condition is a second to the condition of the condition of the condition is a second to the condition of the co	except for formal matters, prose	ecution as to the merits is
Disposition of Claims	,	222,10, 7000 0151 11, 700	0.0. 210.
4) 💢 Claim(s) <u>1-9</u>		is/are	e pending in the application.
	claim(s)		
			is/are rejected.
8) Claims		are subject to restric	ction and/or election requirement
Application Papers		,	and the state of t
9) The specification	is objected to by the Examiner.		
10) ☐ The drawing(s) fil	ed onis/are	a) ☐ accepted or b) ☐ objecte	d to by the Examiner.
	t request that any objection to the d		
			b) disapproved by the Examiner.
	cted drawings are required in reply t		
	ration is objected to by the Exami	ner.	
Priority under 35 U.S.C. §			
	t is made of a claim for foreign pr	iority under 35 U.S.C. § 119(a)-	·(d) or (f).
a) □ All b) □ Some			
	ies of the priority documents have		
	ies of the priority documents have		
аррііс	e certified copies of the priority do cation from the International Burea cailed Office action for a list of the	iu (PCT Rule 17.2(a)),	this National Stage
	t is made of a claim for domestic		al
	of the foreign language provisional		5).
	t is made of a claim for domestic		and/or 121.
Attachment(s)	·	,	
Notice of References Cited (PT		4) Interview Summary (PTO-413) Paper N	o(s)
2) Notice of Draftsperson's Paten		5) Notice of Informal Patent Application (F	PTO-152)
3) Information Disclosure Stateme	nt(s) (PTO-1449) Paper No(s).	6) Other:	

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DETAILED ACTION

Continued Examination Under 37 CFR 1.114

A request for continued examination under 37 CFR 1.114, including the fee set forth in 37 CFR 1.17(e), was filed in this application after final rejection. Since this application is eligible for continued examination under 37 CFR 1.114, and the fee set forth in 37 CFR 1.17(e) has been timely paid, the finality of the previous Office action has been withdrawn pursuant to 37 CFR 1.114. Applicant's submission filed on 12/13/02 has been entered.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 4-6, 8,9 are rejected under 35 U.S.C. 103(a) as being unpatentable over Tanaguchi Tadatake (jp-05090624) in combination with Militsky et al.

Taniguchi teaches depositing CdTe on PET wherein transition temperature is less than 200 C. Tanicguchi does not discloses annealing the CdTe. Mitlitsky discloses a method of annealing

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CdTe.. Taniguchi et al teaches coating of CdTe from the mixture solvent CdTe powder .

Choosing CdTe particle diameter average with the range of 3-5 nm would have been well with in the one of ordinary skill in the art depending on the conversion efficiency of the solar cell. It would have been obvious to one of ordinary skill in the art to anneal CdTe in the invention of Taniguchi et al because annealing increasing the photoelectric conversion efficiency of the solar cell.

Claims 4-6 are rejected under 35 U.S.C. 103(a) as being unpatentable over Militsky in combination with Takenouchi et al. .

Mitlitsky et al discloses a product of forming solar cell device by the following process steps: Providing low temperature plastic material such as polyethersulfone (PES), and such plastic material is incapable of sustaining process temperature of higher than 180 C and such materials are called low temperature substrates and such plastic material have glass transition temperature of not greater than 180 C (see col. 3, lines 1-45).

Mitlitsky et al do not disclose PET or PEN as low temperature substrate. Takenouchi et al discloses a product of photovoltaic devices using low temperature substrates such as polyethylene terepthalate (PET)or (polyethylene sulfone(PES). It would have been obvious to replace PET

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substrate of Takenouchi et al with PES substrate of Mitlitsky et al, because both PES and PET are functionally equivalent as taught by Takenouchi et al.

Claims 1-3 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mitlitsky et al in combination with Takenouchi et al.

Providing low temperature plastic material such as polyethersulfone (PES), and such plastic material are in capable of sustaining process temperature of higher than 180 C and such materials are called low temperature substrates. Mitlitsky et al further disclose depositing a photovoltaic film such as CdTe at a temperature in the range of 100-150 C so that evaporation technique does not exceed the temperature of the substrate greater than 180 C, and then performing laser pulse heating a t a temperature of (see col. 3, lines 1-45). Mitlitsky et al performs pulsed laser annealing to crystallize the CdTe at very high temperature as high as 900 C without heating and damaging the underlying low temperature plastic substrate(see col. 4, lines 59-67). Mitlitsky uses plastic substrate of 25 microns(see col. 5, lines 5-7) and time period for laser heating 100 microseconds, which is less than claimed time period of 0.01 sec to 1 sec and also power is not same as power in Mitlitsky et al. However, such power of the pulse laser energy and time period depends on the thickness of the substrate and thickness of the photovoltaic layer etc., . The choice of selecting the power and time period of pulse laser exposure would have been well within the scope of one of ordinary skill in the art depending on the thickness of the substrate and thickness of the photovoltaic layer etc. The crux of the instant invention is depositing CdTe at

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lower than transition temperature of the plastic material such as PET and not damaging the plastic substrate by exposing the laser at temperature higher than transition temperature and very short period of time. Mitlitsky et al does not teach using PET as a substrate.

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Takenouchi et al discloses using the substrate as PET or PES. It would have been obvious to one of ordinary skill in the art to replace PES with PET because Takenouchi discloses the art recognized equivalents as substrate material for the process solar cells. PET as a substrate material used in Takanouchi et al must be conductive and transparent.

Double Patenting

1. The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d

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887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321© may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

2. Claims 1-6 are provisionally rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 1-10 of copending Application No. 09/890,393. Although the conflicting claims are not identical, they are not patentably distinct from each other because the scope of the instant claim limitations in instant application is encompassed by the claim limitation of the copending application, wherein in instant claims call for CdTe active layer

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deposited of thickness almost 30 microns on PET or PEN substrate with glass transition temperature from 90 C to 200 C and substrate thickness of at least 60 microns and annealing at least 250 C and in the range of 400 C -600 C. The difference is copending claim 1 has a recitation of "tempering by plasma" and instant claim 1 with limitation of "annealing with laser". However, such plasma as recited in copending claim 1 is produced by laser as recited in claim 4 of copending application, which is covered by limitation of "annealing laser of the instant claim 1. Similarly, product claim of the instant claim 4 of CDTE deposited on PET or PEN is encompassed by the product claim 8 of copending application

This is a <u>provisional</u> obviousness-type double patenting rejection because the conflicting claims have not in fact been patented.

In view of the arguments and remarks made by the applicant, where Mitlitsky does not use the substrate with glass transition temperature in the range of 90 C to 200 C, reaction is changed to obvious ness type rejection as modified by Takenouchi et al because Takenouchi discloses the functional equivalence of PES or

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PET. Mitlitsky et al as modified by the teaching of Takenouchi et al would have PET as substrate.

Applicant's arguments filed on 12/13/02 have been fully considered but they are not persuasive. Rejection on claims 4-6, 8,9 over Taniguchi as modified Mitlitsky. Applicants arguments over coating temperature and annealing temperature and time in view of the Takenouchi teaching instability of PET over PES to modify the teaching Mitlitsky is not convincing. However, Takenouchi clearly mention either PET. or PES are art recognized equivalents as low temperature substrates to grow photovoltaic cells.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to S. Mulpuri whose telephone number is (703) 305-5184. The fax phone number for the organization where this application or proceeding is assigned is (703) 308-7722.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

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SAVITRI MULPURI PRIMARY EXAMINER